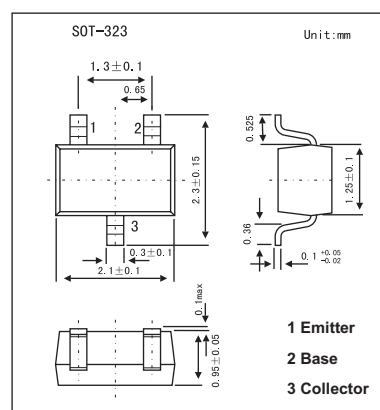


PNP Silicon Epitaxial Transistor

2SA1612

■ Features

- High DC current gain



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CB0}	-120	V
Collector to emitter voltage	V_{CEO}	-120	V
Emitter to base voltage	V_{EB0}	-5	V
Collector current (DC)	I_C	-50	mA
Total power dissipation	P_T	150	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -120V, I_E = 0$			-50	nA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-50	nA
DC current gain	h_{FE}	$V_{CE} = -6V, I_C = -1mA$	135	500	900	
		$V_{CE} = -6V, I_C = -0.1mA^*$	100	500		
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$		-0.09	-0.3	V
Base-emitter voltage	V_{BE}	$V_{CE} = -6V, I_C = -1mA$	-0.55	-0.61	-0.65	V
Gain bandwidth product	f_T	$V_{CE} = -6V, I_E = -1mA$	50	90		MHz
Output capacitance	C_{ob}	$V_{CB} = -30V, I_E = 0, f = 1.0MHz$		2	3	pF

*. $PW \leq 350\mu s$, duty cycle $\leq 2\%$

■ h_{FE} Classification

Marking	C15	C16	C17	C18
h_{FE}	135~270	200~400	300~600	450~900